

WHAT IS CLAIMED IS:

1. A semiconductor light-emitting device comprising:  
a semiconductor light-emitting device chip including a chip  
substrate and a stack formed of semiconductor layers stacked on a surface of  
said chip substrate; and

5 a mount member having a mount surface, wherein  
said semiconductor light-emitting device chip is connected to the  
mount surface of said mount member with said stack facing said mount  
surface, and

10 said mount member includes a material higher in thermal expansion  
coefficient than a material for said chip substrate.

2. A semiconductor light-emitting device comprising:  
a semiconductor light-emitting device chip including a chip  
substrate and a stack formed of semiconductor layers stacked on a surface of  
said chip substrate; and

5 a mount member having a mount surface, wherein  
said semiconductor light-emitting device chip is connected to the  
mount surface of said mount member with said stack facing said mount  
surface, and

10 said mount surface is curved to protrude and said semiconductor  
light-emitting device chip is curved along and connected to said mount  
surface.

3. The semiconductor light-emitting device according to claim 1,  
wherein

said chip substrate includes nitride-based compound semiconductor  
and said stack includes nitride-based compound semiconductor.

4. The semiconductor light-emitting device according to claim 3,  
wherein

said mount member includes at least one of iron and copper.

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5. The semiconductor light-emitting device according to claim 1,  
wherein

said mount surface and said stack are connected by solder and said  
solder includes at least one selected from the group consisting of In, Sn, Pb  
and Au.

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10087372.030100  
201009 2/8/2007